

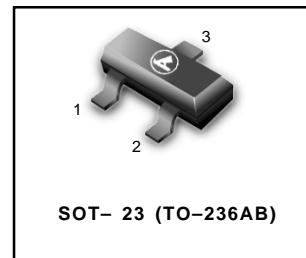
Digital transistors (built-in resistors)

LDTD114ELT1

●Features

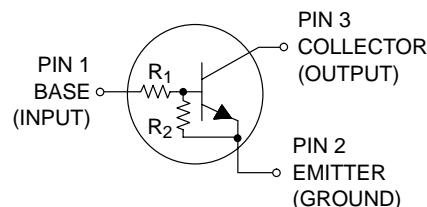
- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.
- 2) The bias resistors consist of thinfilm resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on/off conditions need to be set for operation, making device design easy.
- 4) Pb-Free package is available.

LDTD114ELT1



●Device marking and ordering information

| Device | Marking | Shipping |
|-----------------------|---------|----------------|
| LDTD114ELT1 | CA | 3000/Tape&Reel |
| LDTD114ELT1G(Pb-Free) | CA | 3000/Tape&Reel |



●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

| Parameter | Symbol | Limits | | Unit |
|----------------------|-----------|----------|--|------|
| Supply voltage | V_{cc} | 50 | | V |
| Input voltage | V_{in} | -10~+40 | | V |
| Output current | I_c | 500 | | mA |
| Power dissipation | P_d | 200 | | mW |
| Junction temperature | T_j | 150 | | °C |
| Storage temperature | T_{stg} | -55~+150 | | °C |

●Electrical characteristics ($T_a = 25^\circ\text{C}$)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|----------------------|--------------|------|------|------|---------------|--|
| Input voltage | $V_{l(off)}$ | — | — | 0.5 | V | $V_{cc}=5\text{V}$, $I_o=100\ \mu\text{A}$ |
| | $V_{l(on)}$ | 3 | — | — | | $V_o=0.3\text{V}$, $I_o=10\text{mA}$ |
| Output voltage | $V_{o(on)}$ | — | 0.1 | 0.3 | V | $I_o/I_i=50\text{mA}/2.5\text{mA}$ |
| Input current | I_i | — | — | 0.88 | mA | $V_i=5\text{V}$ |
| Output current | $I_{o(off)}$ | — | — | 0.5 | μA | $V_{cc}=50\text{V}$, $V_i=0\text{V}$ |
| DC current gain | G_i | 56 | — | — | — | $V_o=5\text{V}$, $I_o=50\text{mA}$ |
| Input resistance | R_1 | 7 | 10 | 13 | k Ω | — |
| Resistance ratio | R_2/R_1 | 0.8 | 1 | 1.2 | — | — |
| Transition frequency | f_T | — | 200 | — | MHz | $V_{ce}=10\text{V}$, $I_e=-50\text{mA}$, $f=100\text{MHz}$ * |

* Transition frequency of the device

LDTD114ELT1

● Electrical characteristic curves

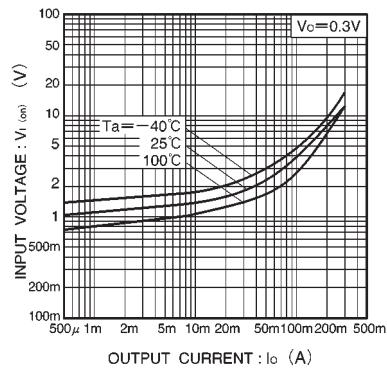


Fig.1 Input voltage vs. output current
(ON characteristics)

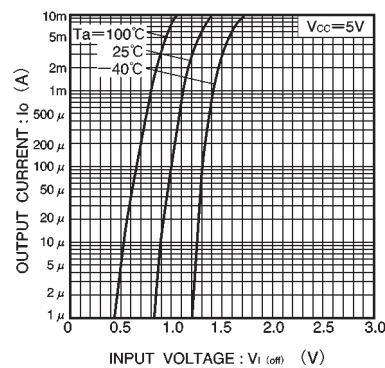


Fig.2 Output current vs. input voltage
(OFF characteristics)

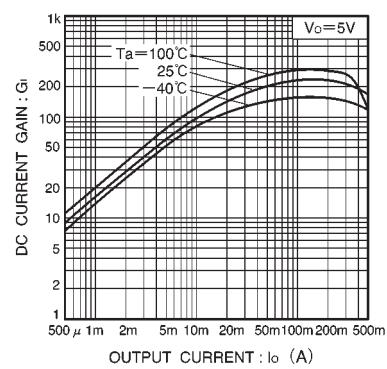


Fig.3 DC current gain vs. output current

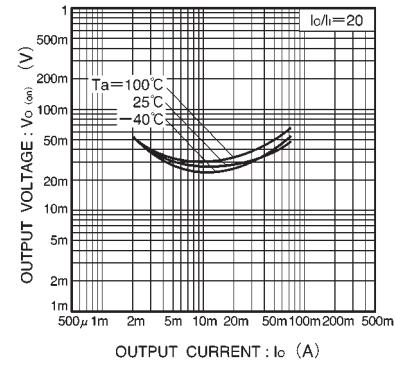
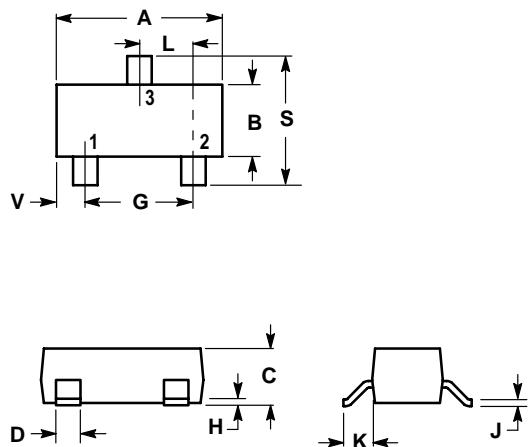


Fig.4 Output voltage vs. output current

LDTD114ELT1
SOT-23

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|--------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.1102 | 0.1197 | 2.80 | 3.04 |
| B | 0.0472 | 0.0551 | 1.20 | 1.40 |
| C | 0.0350 | 0.0440 | 0.89 | 1.11 |
| D | 0.0150 | 0.0200 | 0.37 | 0.50 |
| G | 0.0701 | 0.0807 | 1.78 | 2.04 |
| H | 0.0005 | 0.0040 | 0.013 | 0.100 |
| J | 0.0034 | 0.0070 | 0.085 | 0.177 |
| K | 0.0140 | 0.0285 | 0.35 | 0.69 |
| L | 0.0350 | 0.0401 | 0.89 | 1.02 |
| S | 0.0830 | 0.1039 | 2.10 | 2.64 |
| V | 0.0177 | 0.0236 | 0.45 | 0.60 |

